

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-12	V
Gate-Source Voltage			V <sub>GSS</sub>	-6	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-3.3 -2.7	A
Continuous Drain Current (Note 5) V <sub>GS</sub> = -2.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-3.0 -2.4	A
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	20	A

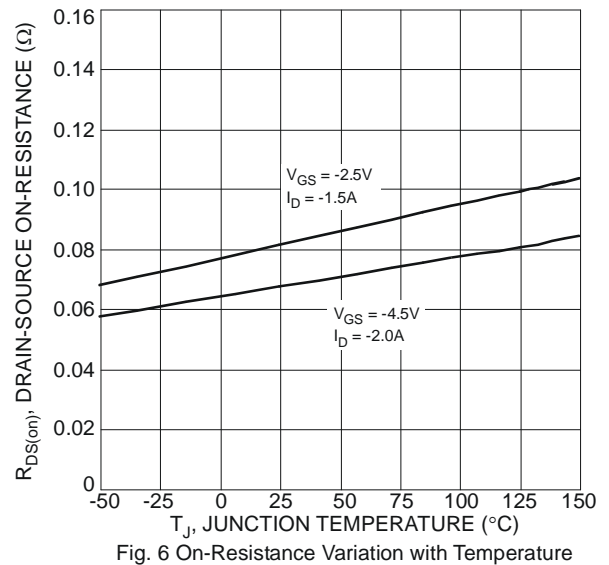
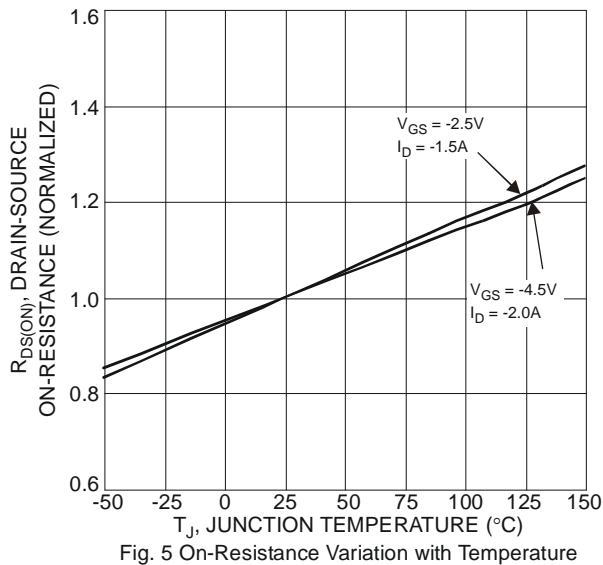
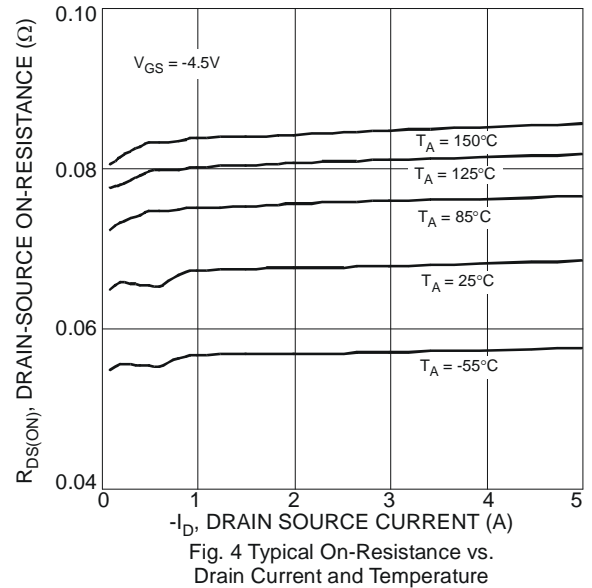
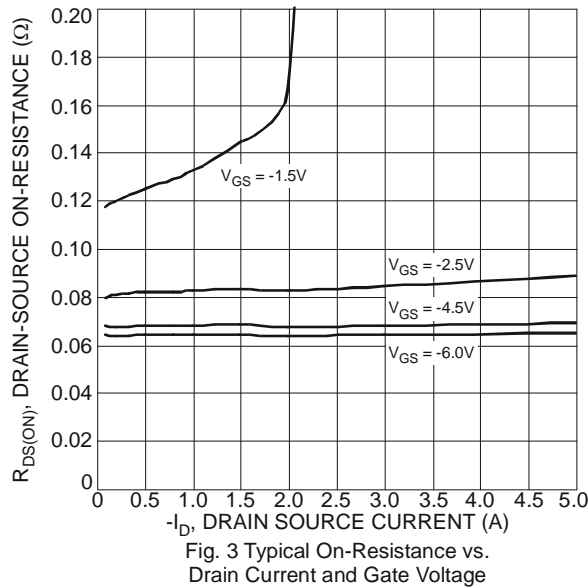
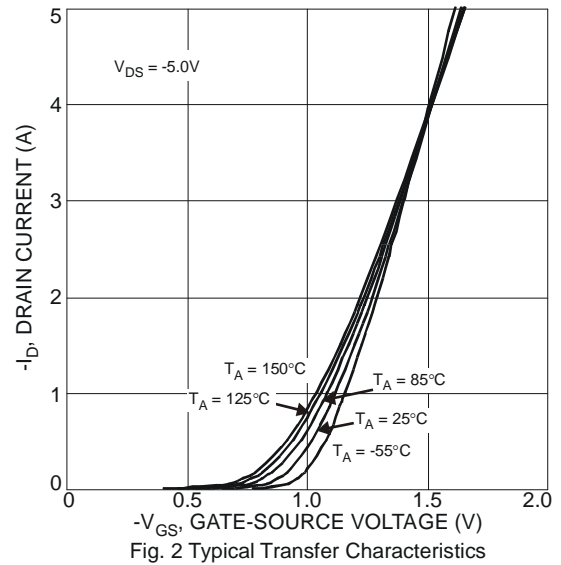
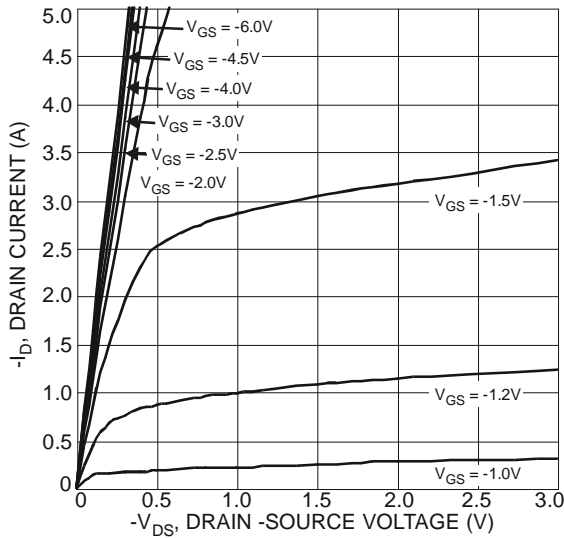
**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	P <sub>D</sub>	0.82	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 7)	R <sub>θJA</sub>	150	°C/W
Thermal Resistance, Junction to Case @T <sub>C</sub> = +25°C (Note 7)	R <sub>θJC</sub>	42.66	°C/W
Power Dissipation (Note 5)	P <sub>D</sub>	1.59	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>θJA</sub>	80.29	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-12	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Gate-Source Breakdown Voltage	BV <sub>GSS</sub>	-6.0	-	-	V	V <sub>DS</sub> = 0V, I <sub>G</sub> = -250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	-	-	-1	μA	V <sub>DS</sub> = -9.6V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	-	-	-100	nA	V <sub>GS</sub> = -6V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.4	-0.6	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	-	65	80	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -500mA
		-	77	93		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -500mA
		-	108	130		V <sub>GS</sub> = -1.5V, I <sub>D</sub> = -500mA
		-	-	-		V <sub>GS</sub> = -1.5V, I <sub>D</sub> = -500mA
Forward Transfer Admittance	Y <sub>fs</sub>	-	4	-	S	V <sub>DS</sub> = -6V, I <sub>D</sub> = -500mA
Diode Forward Voltage	V <sub>SD</sub>	-	-0.6	-1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -500mA
Reverse Recovery Charge	Q <sub>rr</sub>	-	2.0	-	nC	V <sub>dd</sub> = -4.0V, I <sub>F</sub> = -0.5A, di/dt = 100A/μs
Reverse Recovery Time	t <sub>rr</sub>	-	9.5	-	ns	
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	-	213	350	pF	V <sub>DS</sub> = -6V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	-	119	250		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	54.4	90		
Total Gate Charge	Q <sub>g</sub>	-	2.5	5	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -6V, I <sub>D</sub> = -500mA
Gate-Source Charge	Q <sub>gs</sub>	-	0.3	-		
Gate-Drain Charge	Q <sub>gd</sub>	-	0.6	-		
Gate Charge at V <sub>th</sub>	Q <sub>g(th)</sub>	-	0.15	-		
Turn-On Delay Time	t <sub>D(on)</sub>	-	16.7	-	ns	V <sub>DS</sub> = -6V, V <sub>GS</sub> = -2.5V, R <sub>G</sub> = 20Ω, I <sub>D</sub> = -500mA
Turn-On Rise Time	t <sub>r</sub>	-	20.6	-		
Turn-Off Delay Time	t <sub>D(off)</sub>	-	38.4	-		
Turn-Off Fall Time	t <sub>f</sub>	-	28.4	-		

- Notes:
- Device mounted on FR4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.
  - Repetitive rating, pulse width limited by junction temperature.
  - Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.



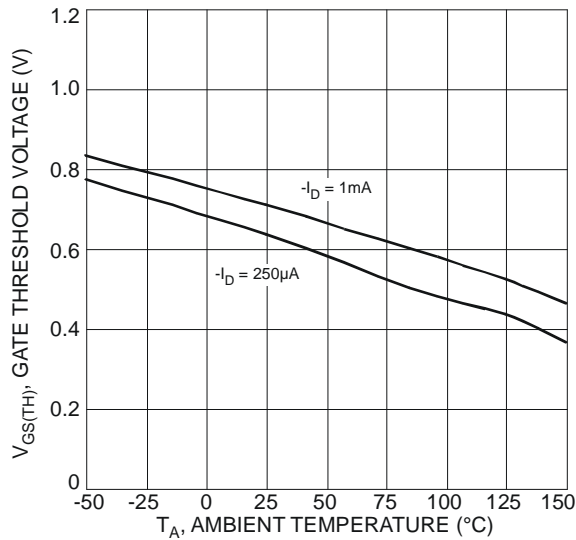


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

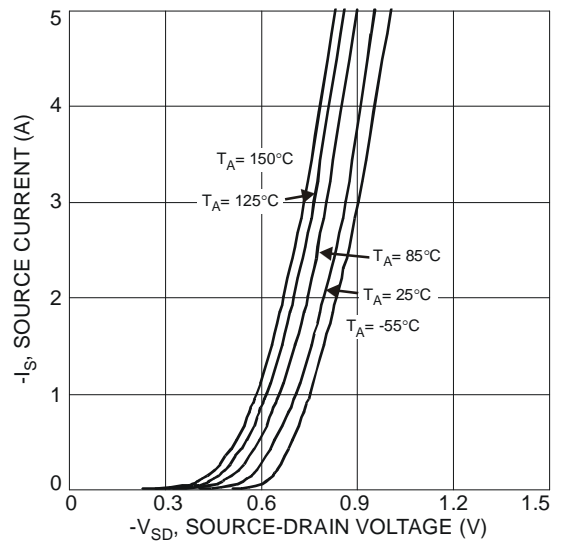


Fig. 8 Diode Forward Voltage vs. Current

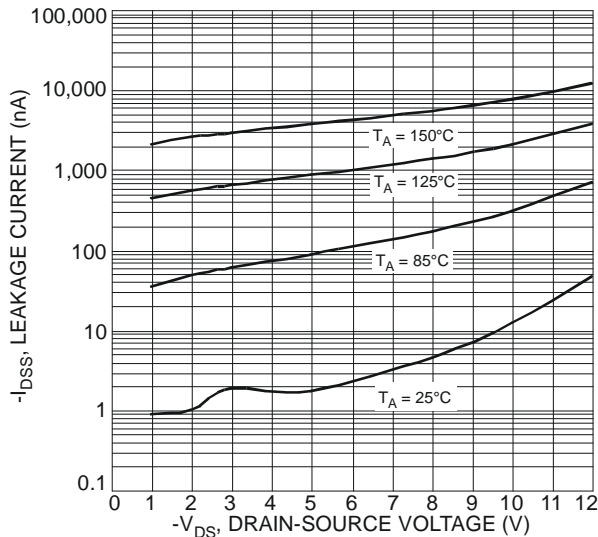


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage

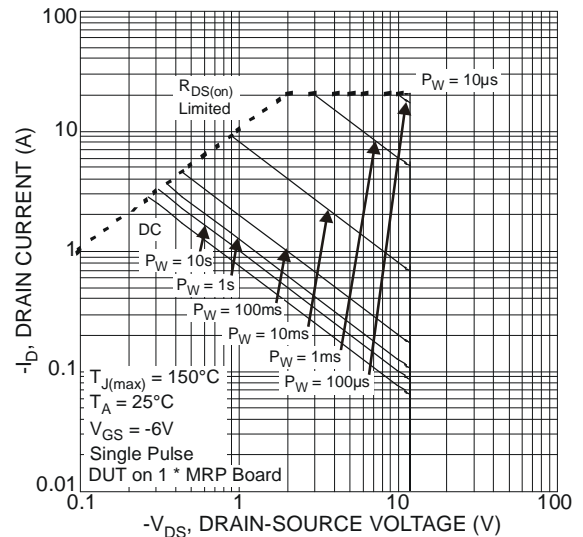


Fig. 10 SOA, Safe Operation Area

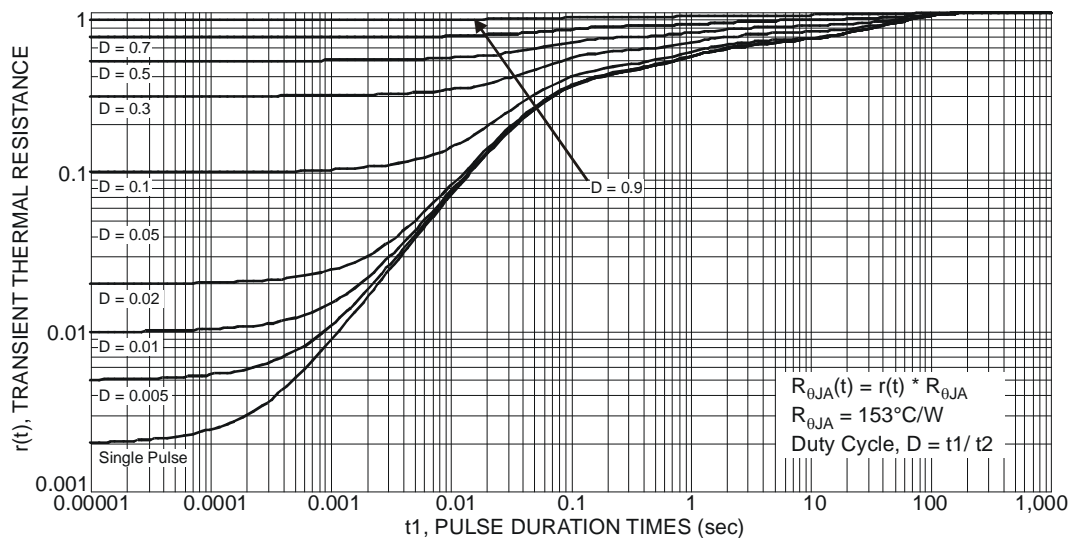
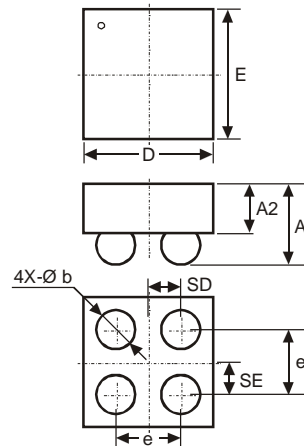


Fig. 11 Transient Thermal Resistance

# Package Outline Dimension

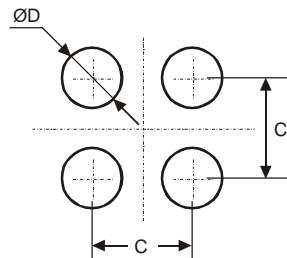
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



U-WLB1010-4			
Dim	Min	Max	Typ
D	0.95	1.05	1.00
E	0.95	1.05	1.00
A	–	0.62	–
A2	–	–	0.38
b	0.25	0.35	0.30
e	–	–	0.50
SD	–	–	0.25
SE	–	–	0.25
All Dimensions in mm			

# Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.50
D	0.25

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